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Description

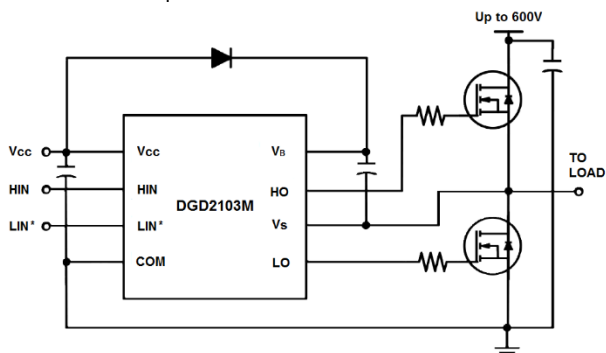
The DGD2103M is a high-voltage / high-speed gate driver capable of driving N-channel MOSFETs and IGBTs in a half-bridge configuration. High voltage processing techniques enable the DGD2103M's high side to switch to 600V in a bootstrap operation.

The DGD2103M logic inputs are compatible with standard TTL and CMOS levels (down to 3.3V) to interface easily with controlling devices. The driver output features high pulse current buffers designed for minimum driver cross conduction. DGD2103M has a fixed internal deadtime of 420ns (typical).

The DGD2103M is offered in the SO-8 (Type TH) package and operates over an extended -40°C to +125°C temperature range.

Applications

- DC-DC Converters
- DC-AC Inverters
- AC-DC Power Supplies
- Motor Controls
- Class D Power Amplifiers



Typical Configuration

Features

- Floating High-Side Driver in Bootstrap Operation to 600V
- Drives Two N-channel MOSFETs or IGBTs in a Half-Bridge Configuration
- Designed for enhanced performance in noisy motor applications
- 290mA Source/600mA Sink Output Current Capability
- Outputs Tolerant to Negative Transients
- Internal Dead Time of 420ns to Protect MOSFETs
- Wide Low Side Gate Driver Supply Voltage: 10V to 20V
- Logic Input (HIN and LIN*) 3.3V Capability
- Schmitt Triggered Logic Inputs
- Undervoltage Lockout for V_{CC} (Logic and Low Side Supply)
- Extended Temperature Range: -40°C to +125°C
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Mechanical Data

- Case: SO-8 (Type TH)
- Case Material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208
- Weight: 0.075 grams (Approximate)



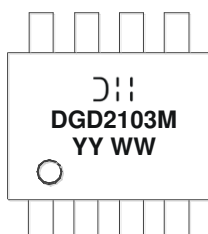
SO-8 (Type TH)
Top View

Ordering Information (Note 4)

Product	Marking	Reel Size (inch)	Tape Width (mm)	Quantity per Reel
DGD2103MS8-13	DGD2103M	13	12	2,500

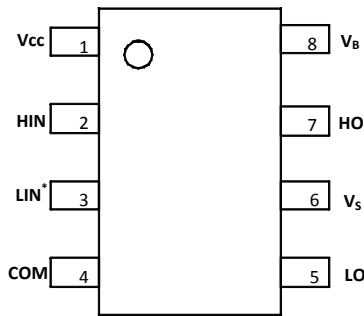
- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



- = Manufacturer's Marking
 DGD2103M = Product Type Marking Code
 YY = Year (ex: 16 = 2016)
 WW = Week (01 to 53)

Pin Diagrams

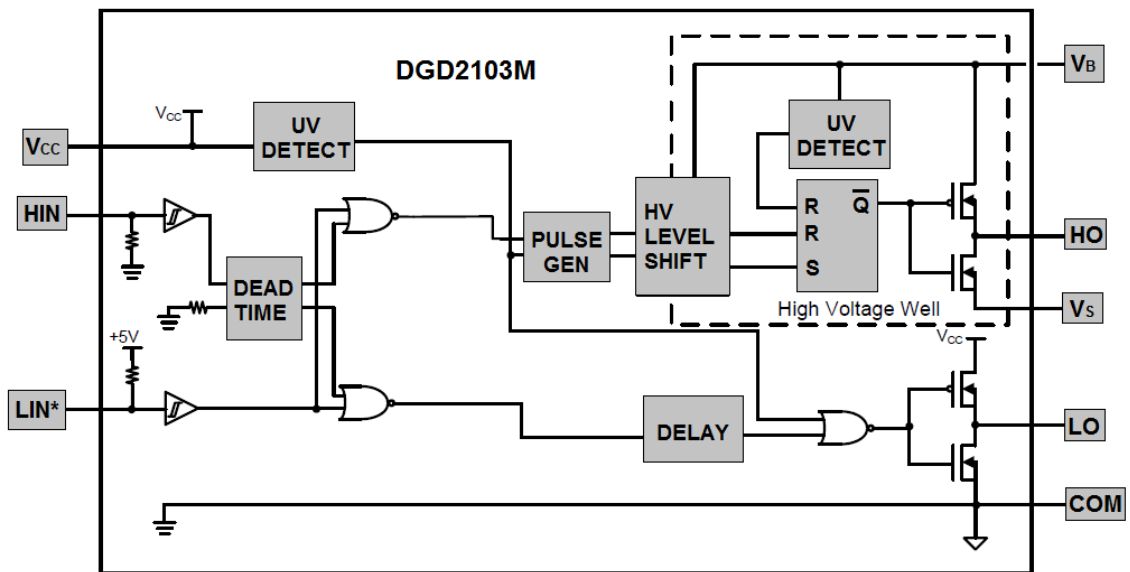


Top View: SO-8 (Type TH)

Pin Descriptions

Pin Number	Pin Name	Function
1	V _{CC}	Logic and Low Side Supply
2	HIN	Logic Input for High-Side Gate Driver Output in Phase with HO
3	LIN*	Logic Input for Low-Side Gate Driver Output out of Phase with LO
4	COM	Low-Side and Logic Return
5	LO	Low-Side Gate Drive Output
6	V _S	High-Side Floating Supply Return
7	HO	High-Side Gate Drive Output
8	V _B	High-Side Floating Supply

Functional Block Diagram



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
High-Side Floating Supply Voltage	V _B	-0.3 to +624	V
High-Side Floating Supply Offset Voltage	V _S	V _B -24 to V _B +0.3	V
High-Side Floating Output Voltage	V _{HO}	V _S -0.3 to V _B +0.3	V
Offset Supply Voltage Transient	dV _S / dt	50	V/ns
Low-Side Fixed Supply Voltage	V _{CC}	-0.3 to +24	V
Low-Side Output Voltage	V _{LO}	-0.3 to V _{CC} +0.3	V
Logic Input Voltage (HIN and LIN*)	V _{IN}	-0.3 to V _{CC} +0.3	V

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor (Note 5)	P _D	0.625	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	200	°C/W
Operating Temperature	T _J	+150	°C
Lead Temperature (Soldering, 10s)	T _L	+300	
Storage Temperature Range	T _{STG}	-55 to +150	

Note: 5. When mounted on a standard JEDEC 2-layer FR-4 board.

Recommended Operating Conditions

Parameter	Symbol	Min	Max	Unit
High Side Floating Supply Absolute Voltage	V _B	V _S + 10	V _S + 20	V
High Side Floating Supply Offset Voltage	V _S	(Note 6)	600	V
High Side Floating Output Voltage	V _{HO}	V _S	V _B	V
Low Side Supply Voltage	V _{CC}	10	20	V
Low Side Output Voltage	V _{LO}	0	V _{CC}	V
Logic Input Voltage (HIN & LIN*)	V _{IN}	0	5	V
Ambient Temperature	T _A	-40	+125	°C

Note: 6. Logic operation for V_S of -5V to +600V. Logic state held for V_S of -5V to -V_{Bs}.

DC Electrical Characteristics (V_{BIAS} (V_{CC} , V_{BS}) = 15V, @ T_A = +25°C, unless otherwise specified.) (Note 7)

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Logic "1" (HIN) & Logic "0" (LIN*) Input Voltage	V_{IH}	2.5	–	–	V	$V_{CC} = 10V$ to 20V
Logic "0" (HIN) & Logic "1" (LIN*) Input Voltage	V_{IL}	–	–	0.8	V	$V_{CC} = 10V$ to 20V
High Level Output Voltage, $V_{BIAS} - V_O$	V_{OH}	–	0.05	0.2	V	$I_O = 2mA$
Low Level Output Voltage, V_O	V_{OL}	–	0.02	0.1	V	$I_O = 2mA$
Offset Supply Leakage Current	I_{LK}	–	–	50	μA	$V_B = V_S = 600V$
Quiescent V_{BS} Supply Current	I_{BSQ}	–	60	100	μA	$V_{IN} = 0V$ or 5V
Quiescent V_{CC} Supply Current	I_{CCQ}	–	350	500	μA	$V_{IN} = 0V$ or 5V
Logic "1" Input Bias Current	I_{IN+}	–	3	10	μA	$HIN = 5V$, $LIN^* = 0V$
Logic "0" Input Bias Current	I_{IN-}	–	–	5	μA	$HIN = 0V$, $LIN^* = 5V$
V_{CC} Supply Undervoltage Positive Going Threshold	V_{CCUV+}	8.0	8.9	9.8	V	–
V_{CC} Supply Undervoltage Negative Going Threshold	V_{CCUV-}	7.4	8.2	9.0	V	–
V_{BS} Supply Undervoltage Positive Going Threshold	V_{BSUV+}	4.5	5.5	6.5	V	–
V_{BS} Supply Undervoltage Negative Going Threshold	V_{BSUV-}	4.2	5.2	6.2	V	–
Output High Short Circuit Pulsed Current	I_{O+}	130	290	–	mA	$V_O = 0V$, $PW \leq 10\mu s$
Output Low Short Circuit Pulsed Current	I_{O-}	270	600	–	mA	$V_O = 15V$, $PW \leq 10\mu s$

Note: 7. The V_{IN} and I_{IN} parameters are applicable to the two logic pins: HIN and LIN*. The V_O and I_O parameters are applicable to the respective output pins: HO and LO.

AC Electrical Characteristics (V_{BIAS} (V_{CC} , V_{BS}) = 15V, $C_L = 1000pF$, @ T_A = +25°C, unless otherwise specified.)

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Turn-On Propagation Delay	t_{ON}	–	680	820	ns	$V_S = 0V$
Turn-Off Propagation Delay	t_{OFF}	–	150	220	ns	$V_S = 600V$
Delay Matching, HO & LO Turn-On / Turn-Off	t_{DM}	–	–	60	ns	–
Turn-On Rise Time	t_R	–	70	170	ns	$V_S = 0V$
Turn-Off Fall Time	t_F	–	35	90	ns	$V_S = 0V$
Deadtime: $t_{DT LO-HO}$ & $t_{DT HO-LO}$	t_{DT}	300	420	650	ns	–

Timing Waveforms

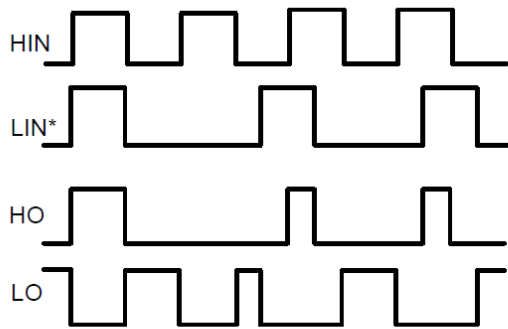


Figure 1. Input / Output Timing Diagram

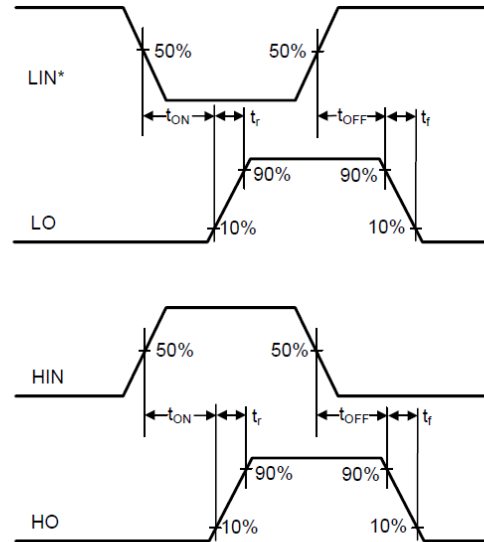


Figure 2. Switching Time Waveform Definitions

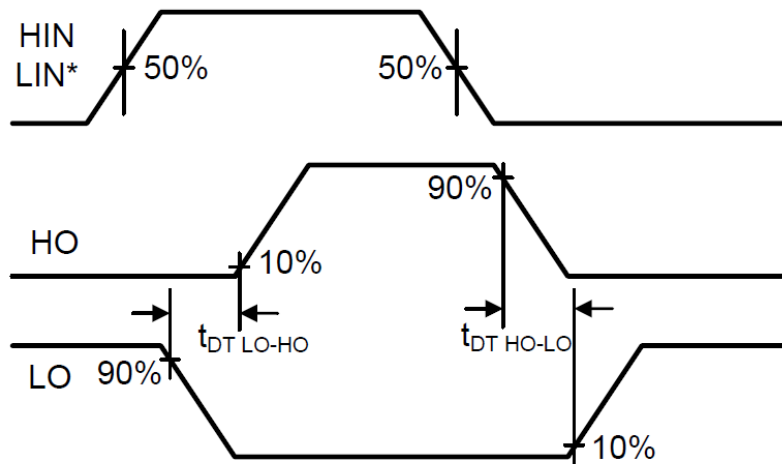


Figure 3. Deadtime Waveform Definitions

Typical Performance Characteristics (@T_A = +25°C, unless otherwise specified.)

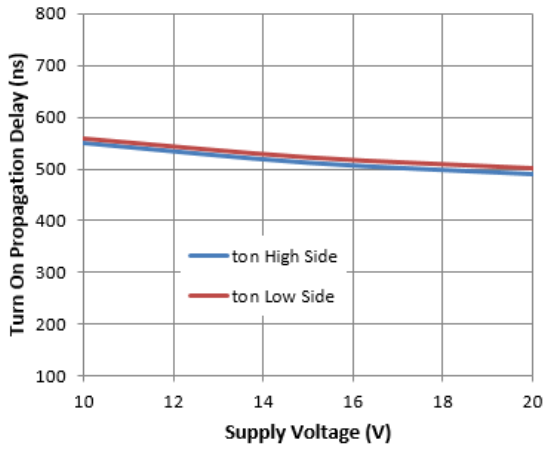


Figure 4. Turn-on Propagation Delay vs. Supply Voltage

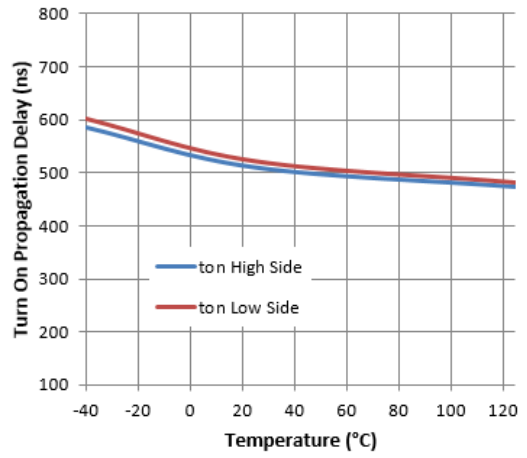


Figure 5. Turn-on Propagation Delay vs. Temperature

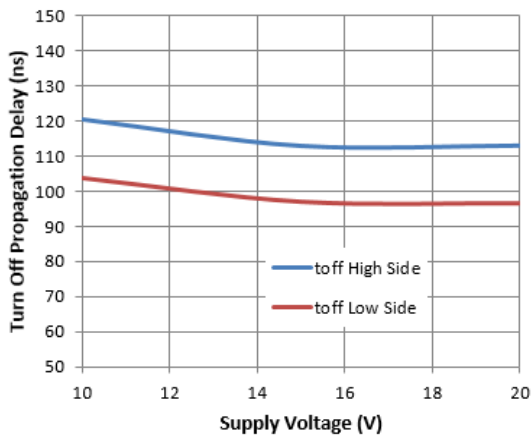


Figure 6. Turn-off Propagation Delay vs. Supply Voltage

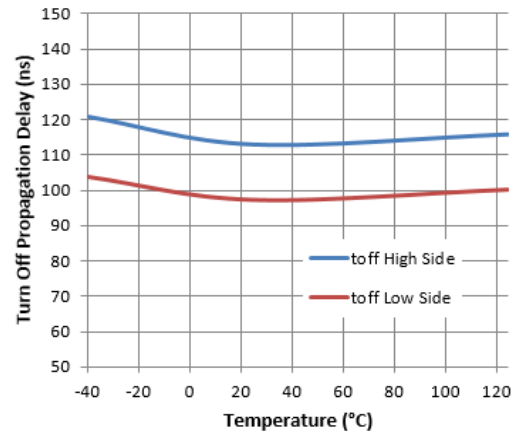


Figure 7. Turn-off Propagation Delay vs. Temperature

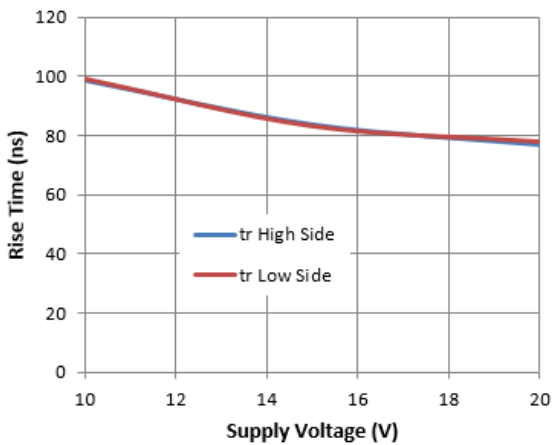


Figure 8. Rise Time vs. Supply Voltage

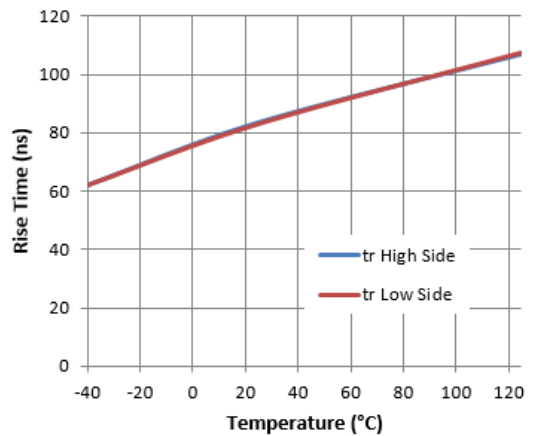


Figure 9. Rise Time vs. Temperature

Typical Performance Characteristics (continued)

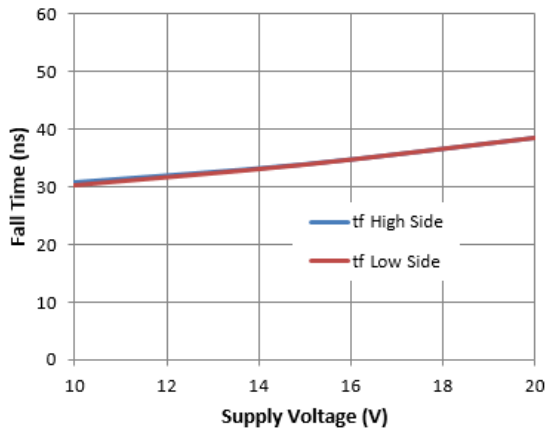


Figure 10. Fall Time vs. Supply Voltage

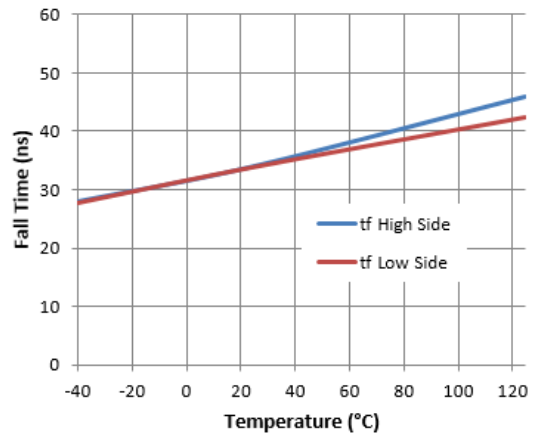


Figure 11. Fall Time vs. Temperature

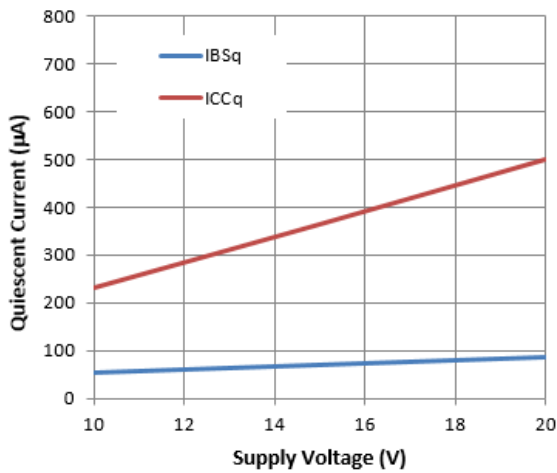


Figure 12. Quiescent Current vs. Supply Voltage

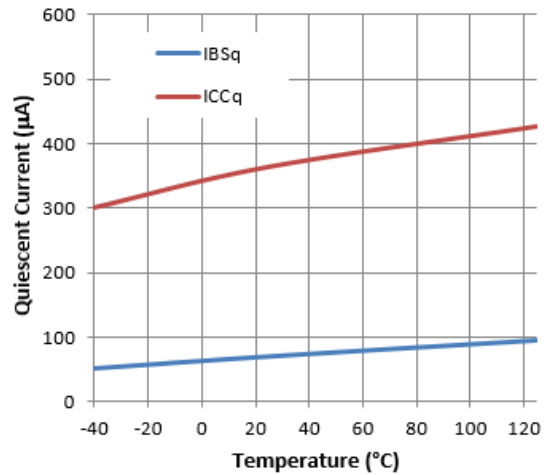


Figure 13. Quiescent Current vs. Temperature

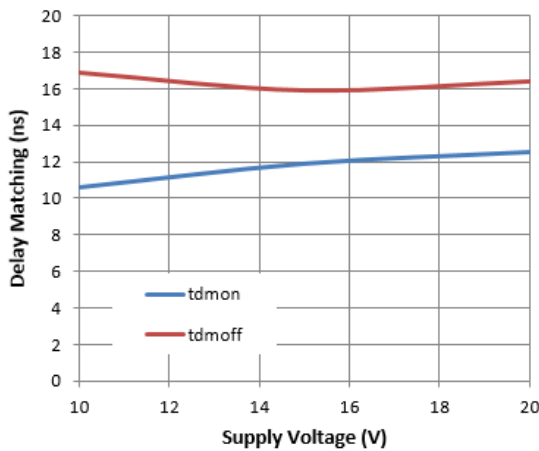


Figure 14. Delay Matching vs. Supply Voltage

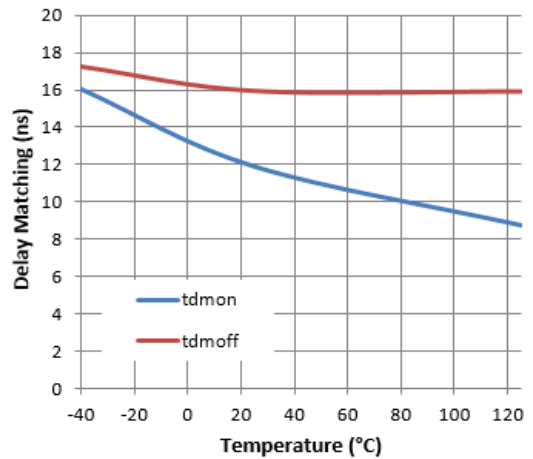


Figure 15. Delay Matching vs. Temperature

Typical Performance Characteristics (cont.)

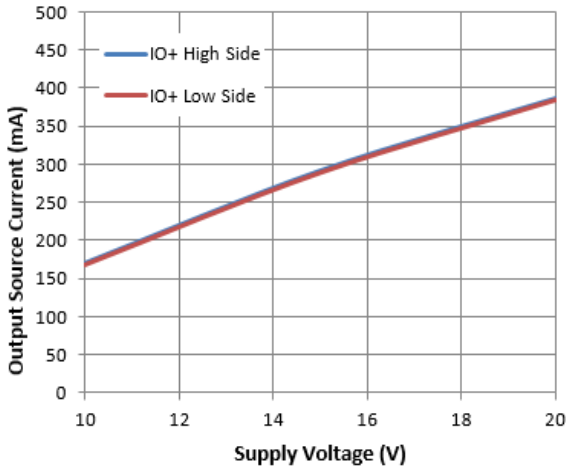


Figure 16. Output Source Current vs. Supply Voltage

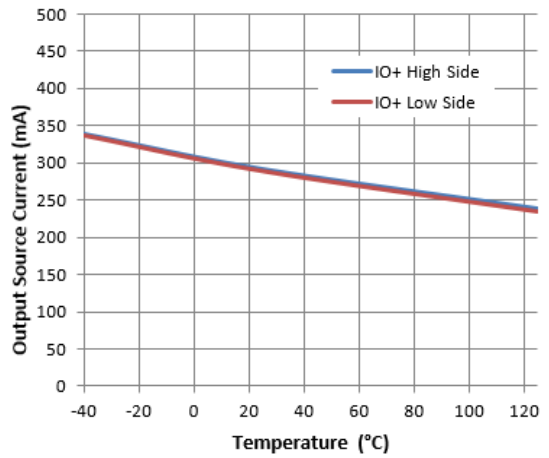


Figure 17. Output Source Current vs. Temperature

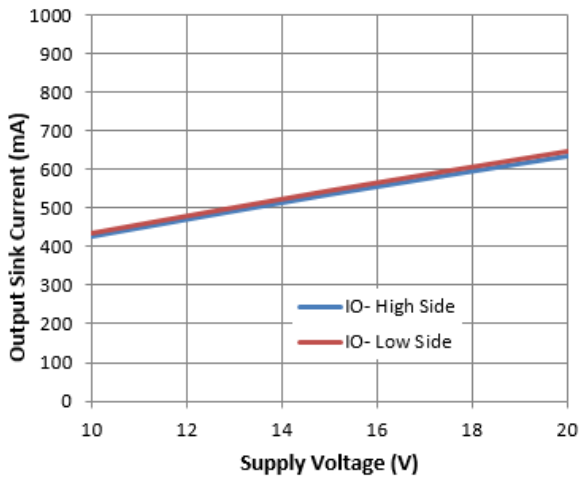


Figure 18. Output Sink Current vs. Supply Voltage

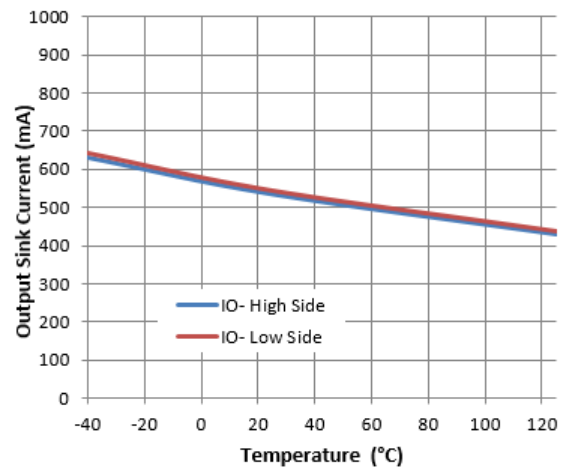


Figure 19. Output Sink Current vs. Temperature

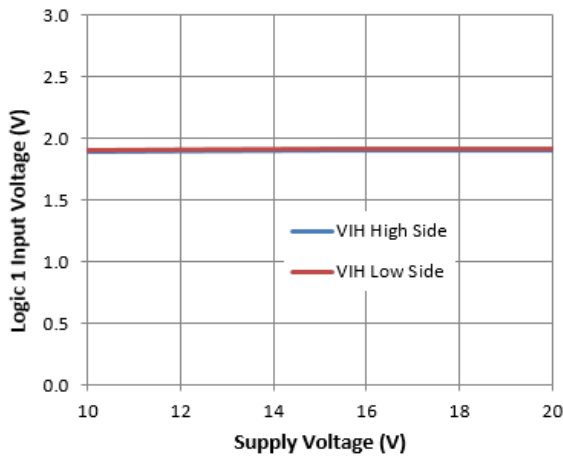


Figure 20. Logic 1 Input Voltage vs. Supply Voltage

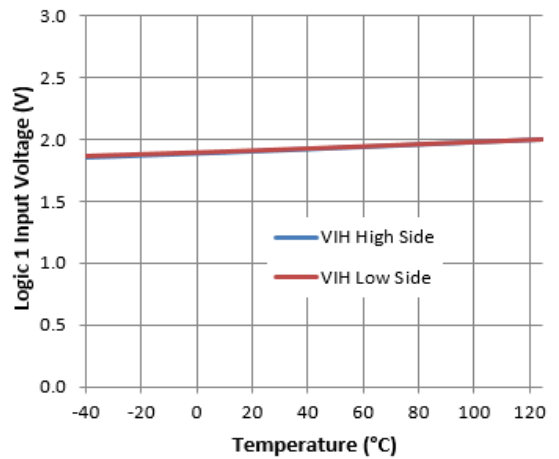


Figure 21. Logic 1 Input Voltage vs. Temperature

Typical Performance Characteristics (cont.)

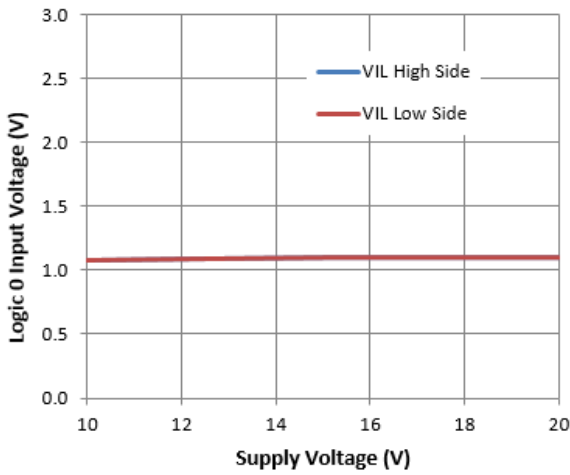


Figure 22. Logic 0 Input Voltage vs. Supply Voltage

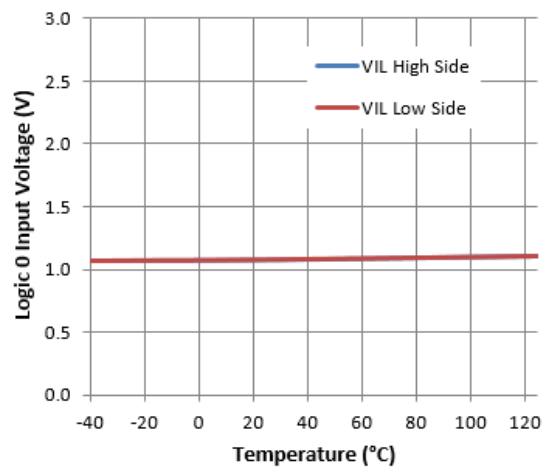


Figure 23. Logic 0 Input Voltage vs. Temperature

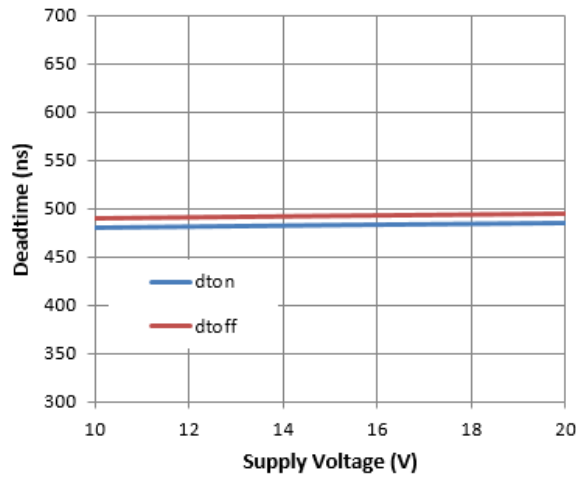


Figure 24. Deadtime vs. Supply Voltage

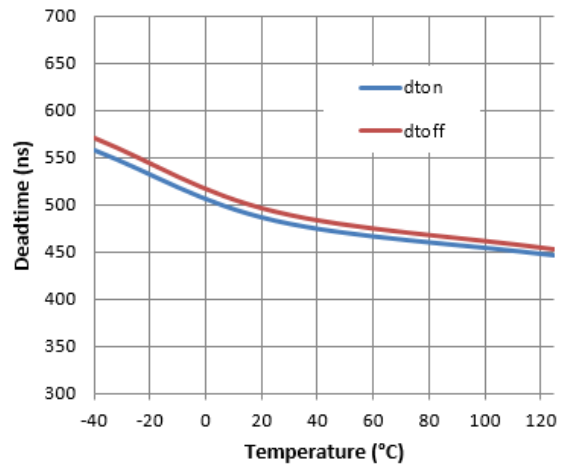


Figure 25. Deadtime vs. Temperature

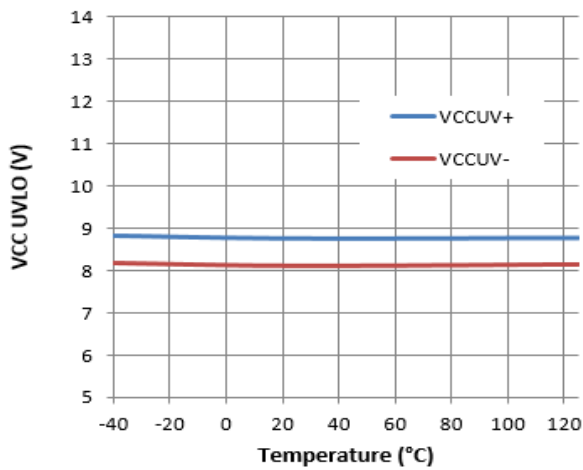


Figure 26. VCC UVLO vs. Temperature

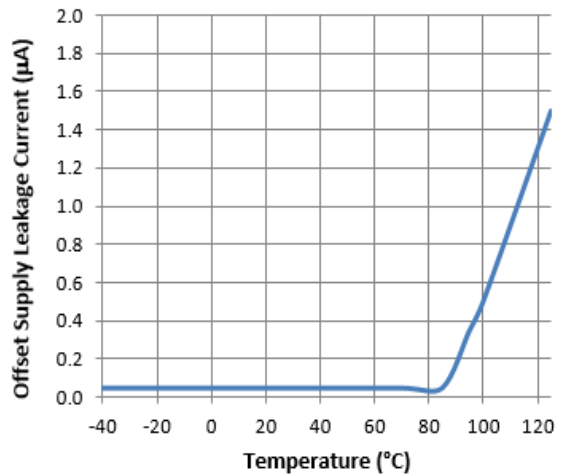
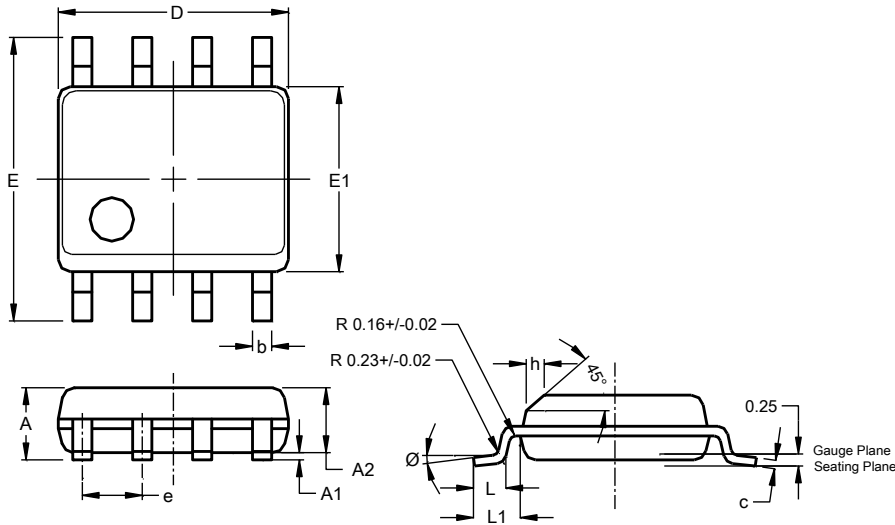


Figure 27. Offset Supply Leakage Current vs. Temperature

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-8 (Type TH)

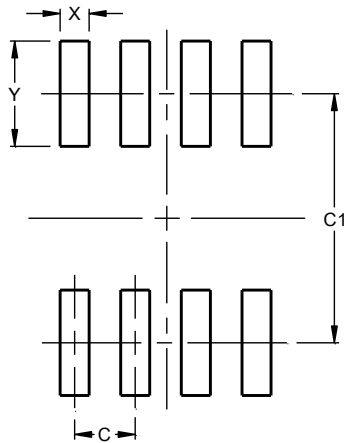


SO-8 (Type TH)			
Dim	Min	Max	Typ
A	1.35	1.75	--
A1	0.10	0.25	--
A2	--	--	1.45
b	0.35	0.51	--
c	0.190	0.248	--
D	4.80	5.00	4.90
E	5.80	6.20	6.00
E1	3.80	4.00	3.90
e	--	--	1.27
h	0.25	0.50	--
L	0.41	1.27	--
L1	--	--	1.04
Ø	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-8 (Type TH)



Dimensions	Value (in mm)
C	1.27
C1	5.20
X	0.60
Y	2.20

Note : For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.

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